捷多邦,专业PCB打样工厂

# 2SC3507

## Silicon NPN triple diffusion planar type

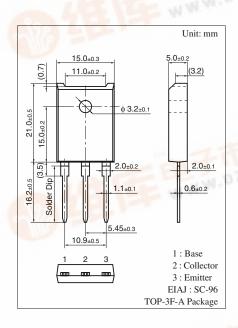
For high breakdown voltage high-speed switching

#### ■ Features

- High-speed switching
- High collector to base voltage V<sub>CBO</sub>
- Satisfactory linearity of forward current transfer ratio h<sub>FE</sub>
- Full-pack package which can be installed to the heat sink with one screw

### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter		Symbol	Rating	Unit	
Collector to base voltage		V <sub>CBO</sub>	1 000	V	
Collector to emitter voltage		V <sub>CES</sub>	1 000	V	
ATA ZELV		$V_{CEO}$	800	V	
Emitter to base voltage		$V_{EBO}$	7	V	
Peak collector current		$I_{CP}$	10	A	
Collector current		$I_C$	5	A	
Base current		$I_{B}$	3	A	
Collector power	$T_C = 25^{\circ}C$	$P_{\rm C}$	80	W	
dissipation	$T_a = 25^{\circ}C$		3		
Junction temperature		T <sub>j</sub>	150	°C	
Storage temperature		$T_{stg}$	-55 to +150	°C	

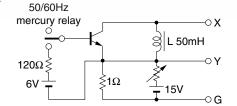


## ■ Electrical Characteristics T<sub>C</sub> = 25°C

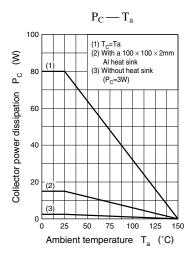
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 1\ 000\ V,\ I_E = 0$			50	μΑ
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 7 \text{ V}, I_{C} = 0$			50	μΑ
Collector to emitter voltage *	V <sub>CEO(sus)</sub>	$I_C = 0.5 \text{ A}, L = 50 \text{ mH}$	800			V
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ A}$	6			
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 0.6 \text{ A}$			1.5	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 0.6 \text{ A}$			1.5	V
Transition frequency	$f_T$	$V_{CE} = 5 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$		6		MHz
Turn-on time	t <sub>on</sub>	$I_C = 3 \text{ A}, I_{B1} = 0.6 \text{ A}, I_{B2} = -1.2 \text{ A},$			1	μs
Storage time	t <sub>stg</sub>	$V_{CC} = 250 \text{ V}$			2.5	μs
Fall time	$t_{\rm f}$				0.5	μs

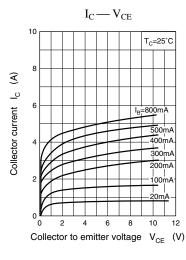
Note) \*: V<sub>CEO(sus)</sub> Test circuit

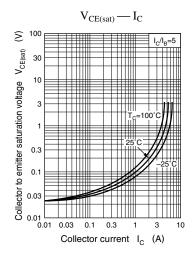


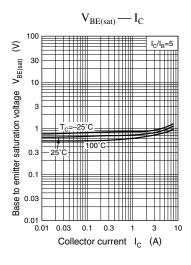


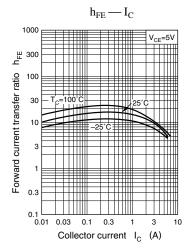
2SC3507 Power Transistors

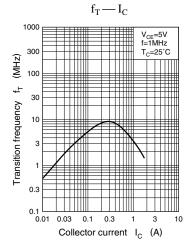


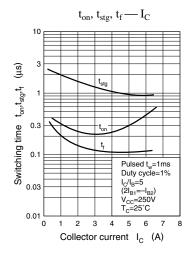


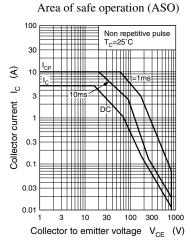






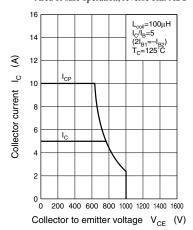




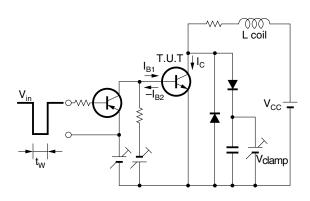


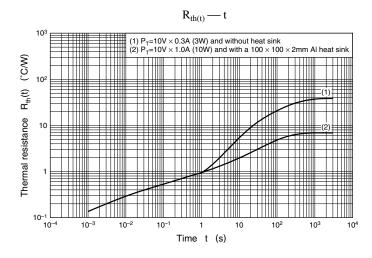
Power Transistors 2SC3507

Area of safe operation, reverse bias ASO



Reverse bias ASO measuring circuit





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